



Microsemi

SCOTTSDALE DIVISION

MMAD1107 and MMAD1107e3

**Switching Diode Array
Steering Diode TVS Arrays™**

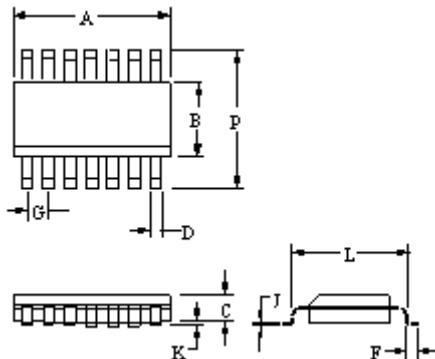
www.Microsemi.com

MMAD1107, e3

SYMBOLS & DEFINITIONS

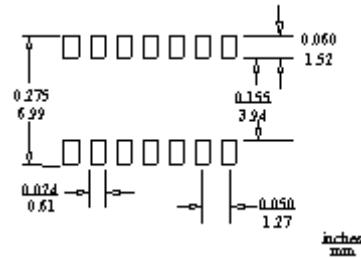
Symbol	Definition
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.
V_F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.
I_R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature.
C	Capacitance: The capacitance of the TVS as defined @ 0 volts at a frequency of 1 MHz and stated in picofarads.

OUTLINE AND CIRCUIT



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.740	0.780	18.80	19.81
B	0.235	0.265	5.969	6.731
C	0.120	0.140	3.048	3.556
D	0.270	0.330	6.858	8.382
E	0.320	0.380	8.128	9.652
F	0.100 BSC		2.540 BSC	
G	0.015	0.021	0.381	0.533
H	0.017	0.023	0.431	0.584
I	0.140	0.160	3.556	4.064
J	0.040	0.070	1.016	1.778

OUTLINE



PAD LAYOUT

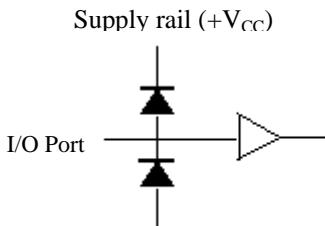
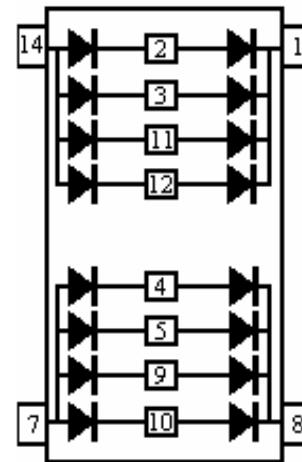


figure 1



CIRCUIT CONFIGURATION